

Doc code :IDS

Doc description: Information Disclosure Statement (IDS) Filed

PTO/SB/08a (03-08)

Approved for use through 07/31/2008. OMB 0651-0031

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INFORMATION DISCLOSURE STATEMENT BY APPLICANT (Not for submission under 37 CFR 1.99)	Application Number		10550853	
	Filing Date		2005-09-22	
	First Named Inventor	MEUNIER-BEILLARD, PHILIPPE		
	Art Unit	2823		
	Examiner Name	NGUYEN, KHIEM D		
	Attorney Docket Number	NL03 0357 US1		

U.S.PATENTS						
Examiner Initial*	Cite No	Patent Number	Kind Code ¹	Issue Date	Name of Patentee or Applicant of cited Document	Pages, Columns, Lines where Relevant Passages or Relevant Figures Appear
/KN/	1	5378651	A	1995-01-03	AGNELLO, PAUL D.; ET AL	
/KN/	2	6251188	B1	2001-06-26	HASHIMOTO, TSUYOSHI; ET AL	

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U.S.PATENT APPLICATION PUBLICATIONS

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/KN/	1	20030003646	A1	2003-01-02	WIEBE BARTELD DE BOER	

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FOREIGN PATENT DOCUMENTS

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/KN/	1	0459122	EP	A2	1991-12-04	INTERNATIONAL BUSINESS MACHINES CORPORATION		<input type="checkbox"/>

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NON-PATENT LITERATURE DOCUMENTS

/Khiem Nguyen/

04/12/2009

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Application Number	10550853
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Examiner Initials*	Cite No	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc), date, pages(s), volume-issue number(s), publisher, city and/or country where published.	T ⁵
/KN/	1	AGNELLO, P.D., ET AL; "HEAVY ARSENIC DOPING OF SILICON GROWN BY ATMOSPHERIC-PRESSURE CHEMICAL VAPOR DEPOSITION AT LOW TEMPERATURES"; APPL. PHYS. LETT. 60 (4); JANUARY 27, 1992; PAGES 454 - 456	<input type="checkbox"/>
↓	2	AGNELLO, P.D., ET AL; "SILICON EPITAXY FROM SILANE BY ATMOSPHERIC-PRESSURE CHEMICAL VAPOR DEPOSITION AT LOW TEMPERATURES"; APPL. PHYS. LETT. 61 (11); SEPTEMBER 14, 1992; PAGES 1298 - 1300	<input type="checkbox"/>
↓	3	YANG, MIN, ET AL; "PHOSPHORUS DOPING AND SHARP PROFILES IN SILICON AND SILICON-GERMANIUM EPITAXY BY RAPID THERMAL CHEMICAL VAPOR DEPOSITION"; JOURNAL OF THE ELECTROCHEMICAL SOCIETY, 147 (9); PAGES 3541 - 3545; JUNE 2, 2000	<input type="checkbox"/>
↓	4	SEDGWICK, T.O., ET AL; "HIGH PHOSPHORUS DOPING OF EPITAXIAL SILICON AT LOW TEMPERATURE AND ATMOSPHERIC PRESSURE"; APPL. PHYS. LETTER. 58 (17); APRIL 29, 1991; PAGES 1896 - 1898	<input type="checkbox"/>
/KN/	5	ALONSO, J.C., ET AL; "LOW-TEMPERATURE EPITAXIAL GROWTH OF UNDOPED AND N-DOPED SILICON BY PHOTOCHEMICAL VAPOR USING DEPOSITION SIH4/SIH2CL2/H2/PH3 MIXTURES"; ELSVIER SEQUOIA S.A. LAUSANEE, CH, VOL 327, NO. 1/2, 1994; PAGES 98-104	<input type="checkbox"/>

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